



#### 45V NPN SMALL SIGNAL TRANSISTOR IN SOT23

#### **Description**

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

#### **Features**

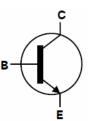
- BV<sub>CEO</sub> > 45V
- I<sub>C</sub> = 0.5A Continuous Collector Current
- I<sub>CM</sub> = 1A Peak Pulse Current
- Complementary PNP Types: BC807-16
- Ideally Suited for Automatic Insertion
- Epitaxial Planar Die Construction
- For switching and AF Amplifier Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

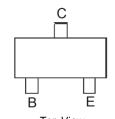
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight 0.008 grams (Approximate)







Device Symbol



Top View Pin-Out

#### Ordering Information (Notes 4 and 5)

| Part number    | Compliance | Marking | Reel size (inches) | Tape width (mm) | Quantity per reel |
|----------------|------------|---------|--------------------|-----------------|-------------------|
| BC817-16Q-7-F  | Automotive | K6A     | 7                  | 8               | 3,000             |
| BC817-40Q-7-F  | Automotive | K6C     | 7                  | 8               | 3,000             |
| BC817-40Q-13-F | Automotive | K6C     | 13                 | 8               | 10,000            |

Notes

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product\_compliance\_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**



XXX = Product Type Marking Code (See table above)

YM = Date Code Marking Y = Year ex: C = 2015

M = Month ex: 9 = September

Date Code Key

| Year  | 2015 | 2016 | 2017 | 2018 | 2019 | 2020 | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 |
|-------|------|------|------|------|------|------|------|------|------|------|------|------|
| Code  | С    | D    | Е    | F    | G    | Н    |      | J    | K    | L    | М    | N    |
| Month | Jan  | Feb  | Mar  | Apr  | May  | Jun  | Jul  | Aug  | Sep  | Oct  | Nov  | Dec  |
|       |      |      |      |      |      |      |      |      |      |      |      |      |

BC817-16Q /-40Q Document number: DS38331 Rev. 2 - 2 1 of 7



### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic            | Symbol           | Value | Unit |
|---------------------------|------------------|-------|------|
| Collector-Base Voltage    | $V_{CBO}$        | 50    | V    |
| Collector-Emitter Voltage | V <sub>CEO</sub> | 45    | V    |
| Emitter-Base Voltage      | $V_{EBO}$        | 5.0   | V    |
| Collector Current         | Ic               | 0.5   | Α    |
| Peak Collector Current    | I <sub>CM</sub>  | 1.0   | Α    |
| Peak Base Current         | I <sub>BM</sub>  | 200   | mA   |

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                 |          | Symbol           | Value       | Unit  |
|--|----------|------------------|-------------|-------|
| Power Dissipation                              | (Note 6) | Ь                | 310         | mW    |
| Power Dissipation                              | (Note 7) | $P_{D}$          | 350         | IIIVV |
| Thormal Desistance, Junction to Ambient        | (Note 6) | ר                | 403         | °C/W  |
| Thermal Resistance, Junction to Ambient        | (Note 7) | $R_{	heta JA}$   | 357         | C/VV  |
| Thermal Resistance, Junction to Leads (Note 8) |          | $R_{	heta JL}$   | 350         | °C/W  |
| Operating and Storage Temperature Range        |          | $T_{J_1}T_{STG}$ | -65 to +150 | °C    |

### ESD Ratings (Note 9)

| Characteristic                             | Symbol  | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 8,000 | ٧    | 3B          |
| Electrostatic Discharge - Machine Model    | ESD MM  | 400   | V    | С           |

Notes:

<sup>6.</sup> For a device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper; device is measured under still air conditions whilst operating in a steady-state.

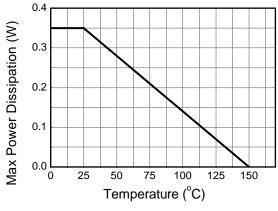
<sup>7.</sup> Same as Note 6, except mounted on 15mm x 15mm 1oz copper.

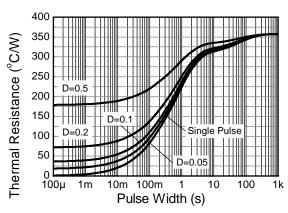
<sup>8.</sup> Thermal resistance from junction to solder-point (at the end of the collector lead).

<sup>9.</sup> Refer to JEDEC specification JESD22-A114 and JESD22-A115.



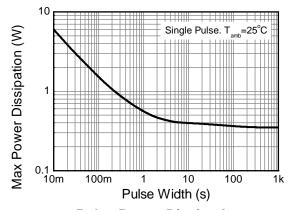
# **Thermal Characteristics and Derating Information**





### **Derating Curve**

**Transient Thermal Impedance** 



**Pulse Power Dissipation** 



# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                 | Characteristic         |                      |            | Тур | Max             | Unit | Test Condition                                 |
|--|------------------------|----------------------|------------|-----|-----------------|------|--|
| Collector-Base Breakdown Voltage               |                        | $BV_{CBO}$           | 50         |     |                 | V    | $I_C = 100 \mu A$                              |
| Collector-Emitter Breakdown Voltage            |                        | $BV_{CEO}$           | 45         | _   | _               | V    | $I_C = 10mA$                                   |
| Emitter-Base Breakdown Voltage                 |                        | $BV_{EBO}$           | 5          |     |                 | V    | $I_{C} = 100 \mu A$                            |
| Collector-Emitter Cut-Off Current              |                        | loro                 |            |     | 100             | nA   | $V_{CE} = 45V$                                 |
| Conector-Emitter Cut-On Current                |                        | ICES                 | _          | _   | 5.0             | μΑ   | $V_{CE} = 25V, T_J = +150$ °C                  |
| Emitter-Base Cut-Off Current                   |                        | I <sub>EBO</sub>     | _          |     | 100             | nA   | $V_{EB} = 5.0V$                                |
|  | BC817-16Q<br>BC817-40Q | h <sub>FE</sub>      | 100<br>250 |     | 250<br>600<br>— |      | V <sub>CE</sub> = 1.0V, I <sub>C</sub> = 100mA |
| DC Current Gain (Note 10)                      | BC817-16Q<br>BC817-40Q |                      | 60<br>170  | _   |                 | _    | V <sub>CE</sub> = 1.0V, I <sub>C</sub> = 300mA |
| Collector-Emitter Saturation Voltage (Note 10) |                        | V <sub>CE(SAT)</sub> | _          | _   | 0.7             | V    | $I_C = 500 \text{mA}, I_B = 50 \text{mA}$      |
| Base-Emitter Voltage (Note 10)                 |                        | $V_{BE}$             | _          | _   | 1.2             | V    | $V_{CE} = 1.0V, I_{C} = 300mA$                 |
| Gain Bandwidth Product                         |                        | f <sub>T</sub>       | 100        |     |                 | MHz  | $V_{CE} = 5.0V, I_{C} = 10mA,$<br>f = 50MHz    |
| Collector-Base Capacitance                     |                        | C <sub>CBO</sub>     | _          | _   | 12              | pF   | V <sub>CB</sub> = 10V, f = 1.0MHz              |

10. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



### Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

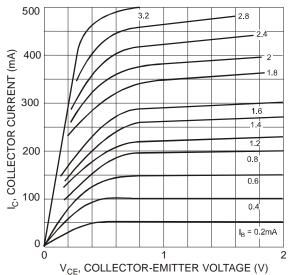


Figure 1 Typical Collector Current vs. Collector-Emitter Voltage

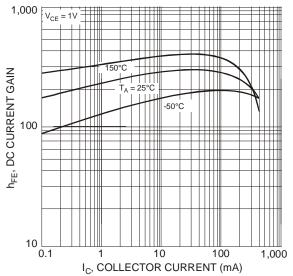


Figure 3 Typical DC Current Gain vs. Collector Current

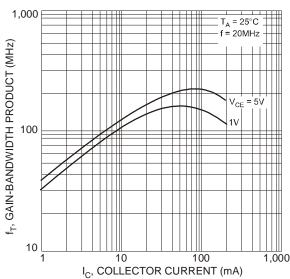


Figure 5 Gain-Bandwidth Product vs. Collector Current

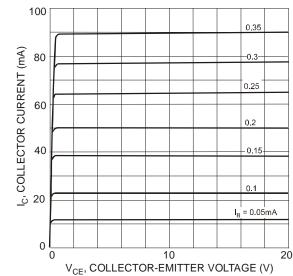


Figure 2 Typical Collector Current vs. Collector-Emitter Voltage

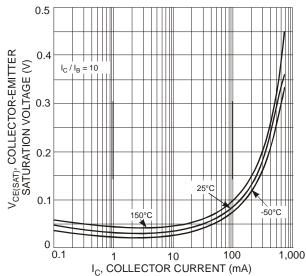


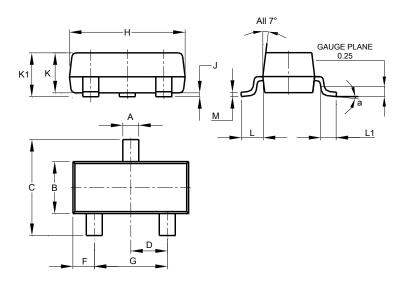
Figure 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23

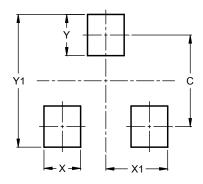


| SOT23 |        |         |       |  |  |  |
|-------|--------|---------|-------|--|--|--|
| Dim   | Min    | Max     | Тур   |  |  |  |
| Α     | 0.37   | 0.51    | 0.40  |  |  |  |
| В     | 1.20   | 1.40    | 1.30  |  |  |  |
| С     | 2.30   | 2.50    | 2.40  |  |  |  |
| D     | 0.89   | 1.03    | 0.915 |  |  |  |
| F     | 0.45   | 0.60    | 0.535 |  |  |  |
| G     | 1.78   | 2.05    | 1.83  |  |  |  |
| Н     | 2.80   | 3.00    | 2.90  |  |  |  |
| J     | 0.013  | 0.10    | 0.05  |  |  |  |
| K     | 0.890  | 1.00    | 0.975 |  |  |  |
| K1    | 0.903  | 1.10    | 1.025 |  |  |  |
| L     | 0.45   | 0.61    | 0.55  |  |  |  |
| L1    | 0.25   | 0.55    | 0.40  |  |  |  |
| M     | 0.085  | 0.150   | 0.110 |  |  |  |
| а     | 0°     | 8°      |       |  |  |  |
| All   | Dimens | ions in | mm    |  |  |  |

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23



| Dimensions | Value (in mm) |
|------------|---------------|
| С          | 2.0           |
| Х          | 0.8           |
| X1         | 1.35          |
| Υ          | 0.9           |
| Y1         | 2.9           |



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